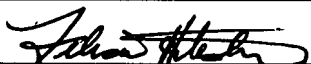


Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126342		APPLICATION NO. New U.S. National Stage of PCT/JP04/007349	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Masahiro SAKURADA et al. FILING DATE December 19, 2005			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FH.	1)	5,919,302	0706/1999	FALSTER et al.	—	—	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
FH.	2)	JP A 2002-057160 w/ abst. & trans	02/22/2002	JAPAN	—	—	
FH.	3)	JP A 2000-313691 w/ abst. & trans	11/14/2000	JAPAN	—	—	
FH.	4)	JP A 11-147786 w/ abstract & trans	06/02/1999	JAPAN	—	—	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
FH.	5)	Voronkov, "The Mechanism of Swirl Defects Formation in Silicon," Journal of Crystal Growth, Vol. 59, pp. 625-643, 1982					
FH.	6)	Dupret et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," Int. J. Heat Mass Transfer, Vol. 33, No. 9, pp. 1849-1871, 1990					
EXAMINER					DATE CONSIDERED 4/27/2007		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 19, 2005